Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-24. (Canceled)
- 25. (Currently Amended) A complementary thin film transistor circuit, comprising:
 - a substrate;

a first thin film transistor that is formed on the substrate, the first thin film transistor including a first semiconductor film, a first gate electrode, and a first gate insulating film disposed between the first semiconductor film and the first gate electrode, the first semiconductor film including a first source region, a first drain region and a first channel region, the first thin film transistor being a first-conductivity-type thin film transistor; and

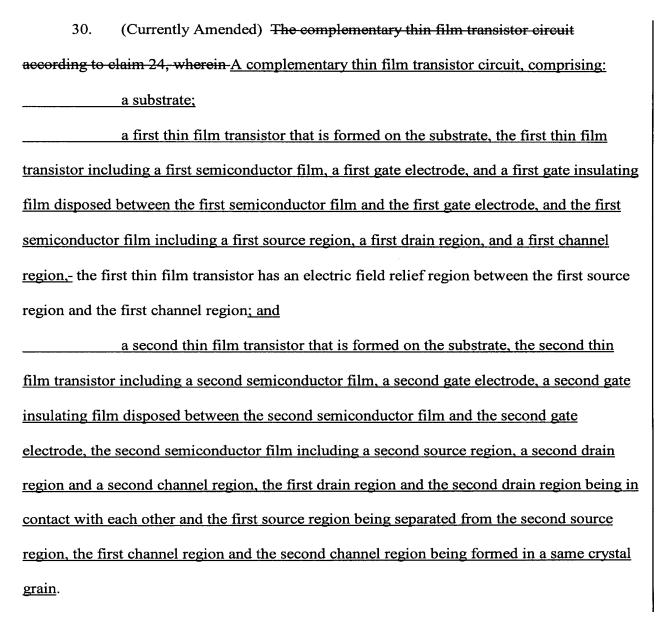
a second thin film transistor that is formed on the substrate, the second thin film transistor including a second semiconductor film, a second gate electrode, a second gate insulating film disposed between the second semiconductor film and the second gate electrode, the second semiconductor film including a second source region, a second drain region, and a second channel region, the second thin film transistor being a second-conductivity-type thin film transistor, the first drain region and the second drain region being in contact with each other, and the first source region and the second source region being in contact with each other, the first channel region and the second channel region being formed in a same crystal grain.

26. (Currently Amended) The complementary thin film transistor circuit according to <u>claim 27</u>elaim 24, further comprising:

a plurality of crystal grains formed on the substrate, each of the plurality of crystal grains being a single crystal grain, one of the plurality of crystal grains including the first semiconductor film and the second semiconductor film.

27.	A complementary thin film transistor circuit, comprising:	
	a substrate;	
	a first thin film transistor that is formed on the substrate, the first thin film	
transistor incl	uding a first semiconductor film, a first gate electrode, and a first gate insulating	
film disposed	between the first semiconductor film and the first gate electrode, and the first	
semiconducto	r film including a first source region, a first drain region, and a first channel	
region;		
	a second thin film transistor that is formed on the substrate, the second thin	
film transistor	including a second semiconductor film, a second gate electrode, a second gate	
insulating filn	n disposed between the second semiconductor film and the second gate	
electrode, the	second semiconductor film including a second source region, a second drain	
region and a s	econd channel region, the first drain region and the second drain region being in	
contact with e	each other and the first source region being separated from the second source	
region, the fir	st channel region and the second channel region being formed in a same crystal	
grain;		
	a first source electrode that is electrically contacting the first source region;	
	a second source electrode that is electrically contacting the second source	
region; and		
	a drain electrode that is electrically contacting the first drain region and the	
second drain region.		

- 28. (Currently Amended) The complementary thin film transistor circuit according to <u>claim 27elaim 24</u>, wherein the first channel region and the second channel region have a same plane orientation.
- 29. (Currently Amended) The complementary thin film transistor circuit according to <u>claim 27</u>elaim 24, wherein the first thin film transistor is a first-conductivity-type thin film transistor and the second thin film transistor is a second-conductivity-type thin film transistor.



31.	(Currently Amended) The complementary thin film transistor circuit
according to c	laim 24, further comprising: A complementary thin film transistor circuit,
comprising:	
	a substrate;
	a first thin film transistor that is formed on the substrate, the first thin film
transistor inclu	ading a first semiconductor film, a first gate electrode, and a first gate insulating
film disposed	between the first semiconductor film and the first gate electrode, and the first
semiconductor	film including a first source region, a first drain region, and a first channel
region;	
	a second thin film transistor that is formed on the substrate, the second thin
film transistor	including a second semiconductor film, a second gate electrode, a second gate
insulating film	disposed between the second semiconductor film and the second gate
electrode, the	second semiconductor film including a second source region, a second drain
region and a so	econd channel region, the first drain region and the second drain region being in
contact with ea	ach other and the first source region being separated from the second source
region, the firs	t channel region and the second channel region being formed in a same crystal
grain; and	
	an insulating film on the substrate, the first thin film transistor and the second
thin film trans	istor being formed on the insulating film, the insulating film having a concave
portion.	
32.	(Currently Amended) An electro-optical device, comprising: